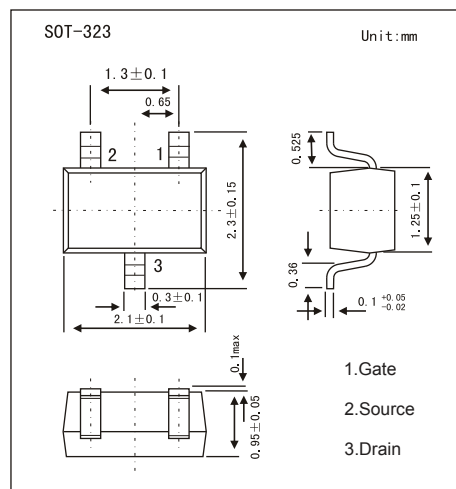
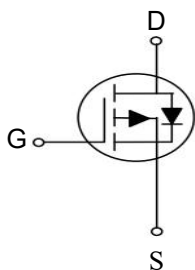


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■ Features

- V_{DS} -30V
- I_D (at $V_{GS}=-10V$) -1.5A
- $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) < 80m Ω
- $R_{DS(ON)}$ (at $V_{GS}=-2.5V$) < 120m Ω



■ Absolute Maximum Ratings

Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±12	V
Drain Current-Continuous ^(Note2)	$T_C=25^{\circ}C$	I_D	-1.5	A
	$T_C=70^{\circ}C$		-1.2	A
-Pulsed ^(Note 1· Note 2)		I_{DM}	-6	A
Maximum Power Dissipation	$T_C=25^{\circ}C$	P_D	0.7	W
	$T_C=70^{\circ}C$		0.56	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^{\circ}C$
Thermal Resistance Junction-Ambient		$R_{\theta JA}$	400	$^{\circ}C/W$

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■ Electrical Characteristics (T_C=25 °C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V , I _D =-250uA	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V , V _{GS} =0V			-1	uA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±12V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250uA	-0.5	-0.9	-1.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-2.5V , I _D =-1.0A		90	120	mΩ
		V _{GS} =-4.5V , I _D =-1.5A		60	80	mΩ
DYNAMIC CHARACTERISTICS Note4						
Input Capacitance	C _{ISS}	V _{DS} =-15V , V _{GS} =0 V , f =1.0MHz		350		pF
Output Capacitance	C _{OSS}			65		pF
Reverse Transfer Capacitance	C _{RSS}			50		pF
Total Gate Charge	Q _g	V _{DS} =-10V , I _D =-1A , V _{GS} =-4.5V		4.8		nC
Gate-Source Charge	Q _{gs}	V _{DS} =-10V , I _D =-1A , V _{GS} =-4.5V		0.5		nC
Gate-Drain Charge	Q _{gd}			1.9		nC
SWITCHING CHARACTERISTICS Note4						
Turn-On Delay Time	t _{D(ON)}	V _{DD} =-10V , I _D =-1A , V _{GS} =-4.5V , R _G =25Ω		3.5		ns
Rise Time	tr			12		ns
Turn-Off Delay Time	tD(OFF)			32		ns
Fall Time	tf			8.5		ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Diode Forward Voltage	V _{SD}	V _{GS} =0V , I _S =-1A			-1	V

Notes:

- 1、 Pulse Test Width < 300us,Duty Cycle< 2%
- 2、 Drain current limited by maximum junction temperature.
- 3、 Guaranteed by design,not subject to production testing.

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■ Typical Performance Characteristics

Fig.1 Continuous Drain Current vs. TC

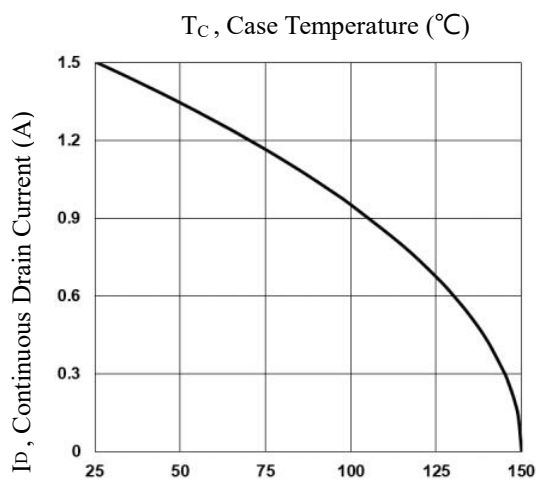


Fig.2 Normalized RDSON vs. TJ

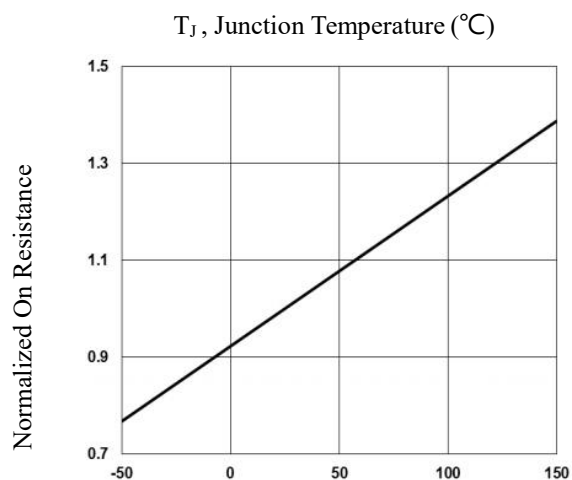


Fig.3 Normalized V_{th} vs. T_J

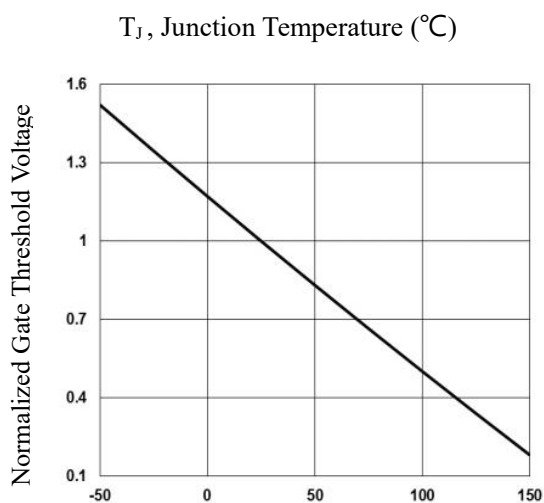


Fig.4 Gate Charge Waveform

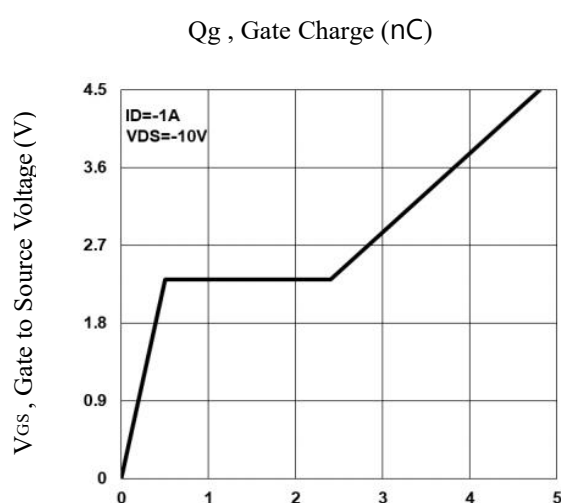


Fig.5 Switching Time Waveform

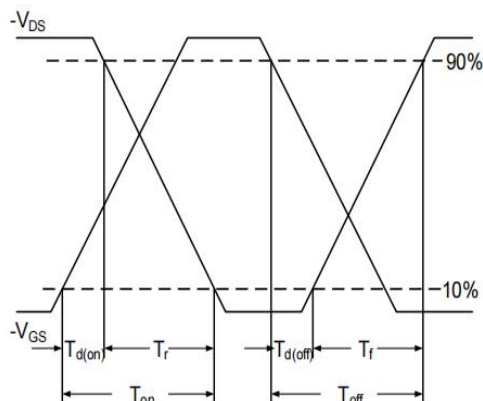
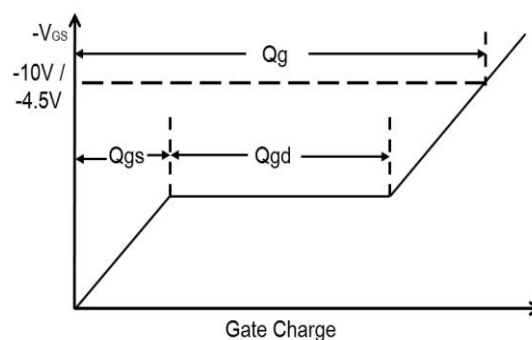


Fig.6 Gate Charge Waveform



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Fig.7 Maximum Safe Operation Area

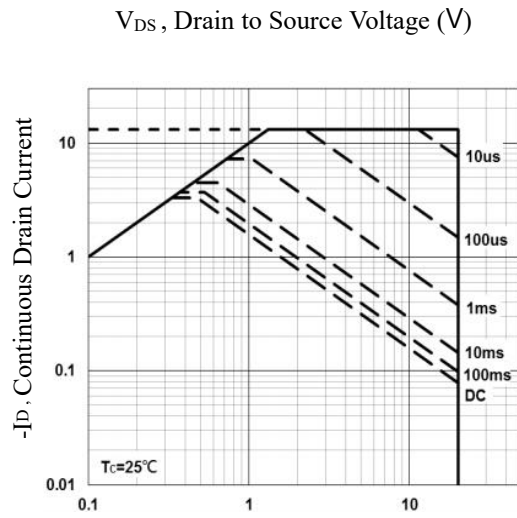


Fig.8 Normalized Transient Impedance

